

## LM615 Quad Comparator and Adjustable Reference

#### **General Description**

**Connection Diagram** 

The comparators have an input range which extends to the negative supply, and have open-collector outputs. Improved over the LM139 series, the input stages of the comparators have lateral PNP input transistors which enable low input currents for large differential input voltages and swings above V+

The voltage reference is a three-terminal shunt-type bandgap, and is referred to the  $V^-$  terminal. Two resistors program the reference from 1.24V to 6.3V, with accuracy of  $\pm$ 0.6% available. The reference features operation over a shunt current range of 17 µA to 20 mA, low dynamic impedance, broad capacitive load range, and cathode terminal voltage ranging from a diode-drop below  $V^-$  to above  $V^+$ .

As a member of National's Super-Block™ family, the LM615 is a space-saving monolithic alternative to a multichip solution, offering a high level of integration without sacrificing performance.

#### **Features**

#### COMPARATORS

- Low operating current Wide supply voltage range 4V to 36V Open-collector outputs
- V<sup>-</sup> to (V<sup>+</sup> 1.8V) Input common-mode range Wide differential input voltage

### REFERENCE

- Adjustable output voltage
- Tight initial tolerance available
- Wide operating current range
- Tolerant of load capacitance

#### Applications

- Adjustable threshold detector
- Time-delay generator
- Voltage window comparator
- Power supply monitor
- RGB level detector



December 1994

600 µA

 $\pm 36V$ 

1.24V to 6.3V

±0.6% (25°C)

17 µA to 20 mA

# M Package FEEDBACK REFERENCE \_ TI /H/11057-24 Top View **Ordering Information**

N Package
1 16
V+ 5 // 12 V-
₀I ┍╾┶╸/╺┵╼┑I <sub>11</sub>
9 REFERENCE
FEEDBACK
TL/H/11057-1 <b>Top View</b>

For information about surface-mount packaging of this device, please contact the Analog Product Marketing group at National Semiconductor Corp. headquarters.

Reference	Temperature Range			NSC Package Number	
Tolerances	$\label{eq:model} \begin{array}{c} \mbox{Military} & \mbox{Industrial} \\ -55^\circ \mbox{C} \leq \mbox{T}_J \leq +125^\circ \mbox{C} & -40^\circ \mbox{C} \leq \mbox{T}_J \leq +85^\circ \mbox{C} \end{array}$		Package		
±0.6% at 25°C, 80 ppm/°C max	LM615AMN	LM615AIN	16-Pin Molded DIP	N16A	
	LM615AMJ/883 (Note 13)		16-Pin Ceramic DIP	J16A	
±2.0% at 25°C, 150 ppm/°C max	LM615MN	LM615IN	16-Pin Molded DIP	N16A	
		LM615IM	16-Pin Narrow Surface Mount	M16A	

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Ratings (Note 1)		
devices are required,	Maximum Junction Temperat	ure 150°C
Semiconductor Sales ty and specifications.	Thermal Resistance, Junction N Package	n-to-Ambient (Note 5) 95°C/W
36\/ (Max)	Soldering Information N Package Soldering (10 s	,
-0.3V (Min)	ESD Tolerance (Note 6)	±1 kV
±20 mA	<b>Operating Tempe</b>	•
±36V	,	$-40^{\circ}C \le T_{J} \le +85^{\circ}C$
(Note 4)	LM615A, LM615M	$-55^{\circ}C \le T_{J} \le +125^{\circ}C$
$-65^{\circ}C \leq T_J \leq +150^{\circ}C$		
	devices are required, Semiconductor Sales ty and specifications. 36V (Max) -0.3V (Min) ±20 mA ±36V (Note 4)	devices are required, Semiconductor Sales ty and specifications.Maximum Junction Temperat Thermal Resistance, Junction N Package36V (Max) -0.3V (Min)Soldering Information N Package Soldering (10 s ESD Tolerance (Note 6)± 20 mA ± 36V (Note 4)± 00 mA ± 36V (Note 4)

**Electrical Characteristics** These specifications apply for V<sup>-</sup> = GND = 0V, V<sup>+</sup> = 5V, V<sub>CM</sub> = V<sub>OUT</sub> = V<sup>+</sup>/2, I<sub>R</sub> = 100  $\mu$ A, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for T<sub>J</sub> = 25°C; limits in **boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typical (Note 7)	LM615AM LM615AI Limits (Note 8)	LM615M LM615I Limits (Note 8)	Units
COMPARA	TORS					
I <sub>S</sub>	Total Supply Current	$ \begin{array}{l} V^+ \text{ Current, } R_{LOAD} = \ \infty, \\ 3V \leq V^+ \ \leq \ 36V \end{array} $	250 <b>350</b>	550 600	600 650	μA max μA max
V <sub>OS</sub>	Offset Voltage over V <sup>+</sup> Range	$4V \leq V^+ \leq 36V, R_L = 15  k\Omega$	1.0 <b>2.0</b>	3.0 <b>6.0</b>	5.0 <b>7.0</b>	mV max mV max
V <sub>OS</sub>	Offset Voltage over V <sub>CM</sub> Range	$\begin{array}{l} 0V \leq V_{CM} \leq (V^+\!-\!1.8V) \\ V^+ = 30V,  R_L = 15  k\Omega \end{array}$	1.0 <b>1.5</b>	3.0 <b>6.0</b>	5.0 <b>7.0</b>	mV max mV max
$rac{\Delta V_{OS}}{\Delta T}$	Average Offset Voltage Drift		15			μV/°C
Ι <sub>Β</sub>	Input Bias Current		-5 - <b>8</b>	25 <b>30</b>	35 <b>40</b>	nA max nA max
I <sub>OS</sub>	Input Offset Current		0.2 <b>0.3</b>	4	4 5	nA max nA max
A <sub>V</sub>	Voltage Gain	$\label{eq:RL} \begin{split} \textbf{R}_L &= 10 \text{ k}\Omega \text{ to } 36 \text{V}, \\ 2 \text{V} &\leq \text{V}_{\text{OUT}} \leq 27 \text{V} \end{split}$	500 <b>100</b>	50	50	V/mV min V/mV
t <sub>R</sub>	Large Signal Response Time	$\label{eq:V+IN} \begin{split} V_{+\text{IN}} &= 1.4\text{V}, V_{-\text{IN}} = \text{TTL} \\ \text{Swing, } \text{R}_{\text{L}} &= 5.1 \text{ k}\Omega \end{split}$	1.5 <b>2.0</b>			μs μs
I <sub>SINK</sub>	Output Sink Current	$V_{+ IN} = 0V, V_{-IN} = 1V,$ $V_{OUT} = 1.5V$	20 13	10 8	10 <b>8</b>	mA min mA min
	$V_{OUT} = 0.4V$	2.8 <b>2.4</b>	1.0 <b>0.5</b>	0.8 <b>0.5</b>	mA min mA min	
IL	Output Leakage Current	$V_{+IN} = 1V, V_{-IN} = 0V,$ $V_{OUT} = 36V$	0.1 <b>0.2</b>	10	10	μA max μA

#### **Electrical Characteristics**

These specifications apply for V<sup>-</sup> = GND = 0V, V<sup>+</sup> = 5V, V<sub>CM</sub> = V<sub>OUT</sub> = V<sup>+</sup>/2, I<sub>R</sub> = 100  $\mu$ A, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for T<sub>J</sub> = 25°C; limits in **boldface type** apply over the **Operating Temperature Range**. (Continued)

Symbol	Parameter	Conditions	Typical (Note 7)	LM615AM LM615AI Limits (Note 8)	LM615M LM615I Limits (Note 8)	Units
VOLTAGE I	REFERENCE (Note 9)					
V <sub>R</sub>	Reference Voltage		1.244	1.2365 1.2515 (±0.6%)	1.2191 1.2689 (±2%)	V min V max
$\frac{\Delta V_{R}}{\Delta T}$	Average Drift with Temperature	(Note 10)	18	80	150	ppm/°C max
$\frac{\Delta V_{R}}{kH}$	Average Drift with Time	$T_{J} = 40^{\circ}C$ $T_{J} = 150^{\circ}C$	400 1000			ppm/kH ppm/kH
$\frac{\Delta V_{R}}{\Delta T_{J}}$	Hysteresis	(Note 11)	3.2			μV/°C
$\frac{\Delta V_R}{\Delta I_R}$	V <sub>R</sub> Change with Current	V <sub>R[100 μA]</sub> – V <sub>R[17 μA]</sub>	0.05 <b>0.1</b>	1 <b>1.1</b>	1 <b>1.1</b>	mV max mV max
		V <sub>R[10 mA]</sub> — V <sub>R[100 μA]</sub> (Note 12)	1.5 <b>2.0</b>	5 <b>5.5</b>	5 <b>5.5</b>	mV max mV max
R	Resistance	ΔV <sub>R</sub> [10 mA to 0.1 mA]/9.9 mA ΔV <sub>R</sub> [100 μA to 17 μA]/83 μA	0.2 0.6	0.56 13	0.56 13	$\Omega$ max $\Omega$ max
$\frac{\Delta V_{R}}{\Delta V_{RO}}$	V <sub>R</sub> Change with V <sub>RO</sub>	$V_{R}[v_{RO} = v_{R}] - V_{R}[v_{RO} = 6.3V]$	2.5 <b>2.8</b>	5 10	5 10	mV max mV max
$\frac{\Delta V_{R}}{\Delta V^{+}}$	V <sub>R</sub> Change with V <sup>+</sup> Change	$V_{R[V+ = 5V]} - V_{R[V+ = 36V]}$	0.1 <b>0.1</b>	1.2 <b>1.3</b>	1.2 <b>1.3</b>	mV max mV max
		$V_{R[V+ = 5V]} - V_{R[V+ = 3V]}$	0.01 <b>0.01</b>	1 1.5	1 1.5	mV max mV max
I <sub>FB</sub>	FEEDBACK Bias Current	$V^- \le V_{FB} \le 5.06 V$	22 <b>29</b>	35 <b>40</b>	50 55	nA max nA max
e <sub>n</sub>	Voltage Noise	BW = 10  Hz to  10  kHz	30			μV <sub>RMS</sub>

Note 1: Absolute maximum ratings indicate limits beyond which damage to the component may occur. Electrical specifications do not apply when operating the device beyond its rated operating conditions.

**Note 2:** Input voltage above  $V^+$  is allowed. As long as one input pin voltage remains inside the common-mode range, the comparator will deliver the correct output. **Note 3:** More accurately, it is excessive current flow, with resulting excess heating, that limits the voltages on all pins. When any pin is pulled a diode drop below  $V^-$ , a parasitic NPN transistor turns ON. No latch-up will occur as long as the current through that pin remains below the Maximum Rating. Operation is undefined and uppredictable when any parasitic diode or transistor is conducting.

Note 4: Shorting an Output to  $V^-$  will not cause power dissipation, so it may be continuous. However, shorting an Output to any more positive voltage (including  $V^+$ ), will cause 80 mA (typ.) to be drawn through the output transistor. This current multiplied by the applied voltage is the power dissipation in the output transistor. To determine junction temperature to exceed 150°C, degraded reliability or destruction of the device may occur. To determine junction temperature, see Note 5.

**Note 5:** Junction temperature may be calculated using  $T_J = T_A + P_D \theta_{JA}$ . The given thermal resistance is worst-case for packages in sockets in still air. For packages soldered to copper-clad board with dissipation from one comparator or reference output transistor, nominal  $\theta_{JA}$  is 80 °C/W for the N package. **Note 6:** Human body model, 100 pF discharge through a 1.5 k $\Omega$  resistor.

Note 7: Typical values in standard typeface are for  $T_J = 25^{\circ}C_i$  values in **boldface type** apply for the full operating temperature range. These values represent the most likely parametric norm.

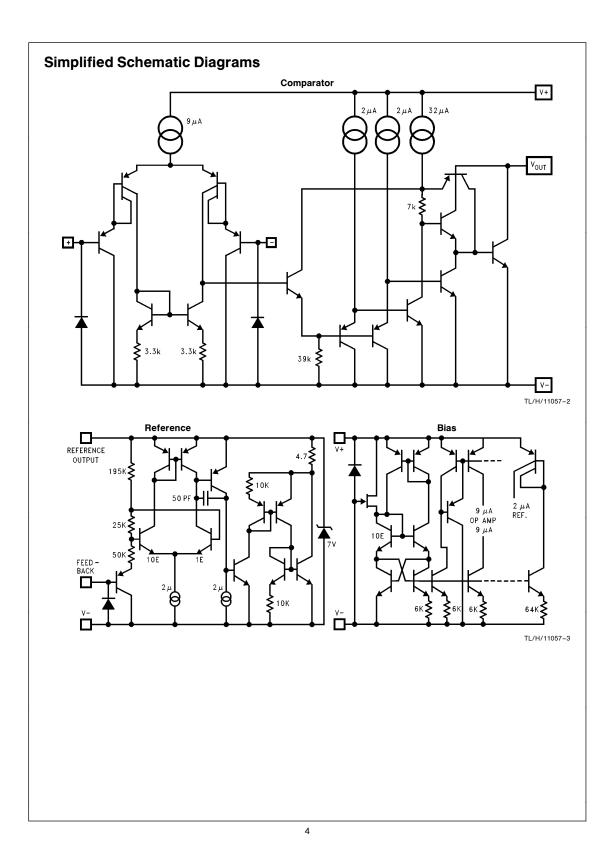
Note 8: All limits are guaranteed for  $T_{,l} = +25^{\circ}C$  (standard type face) or over the full operating temperature range (**bold type face**).

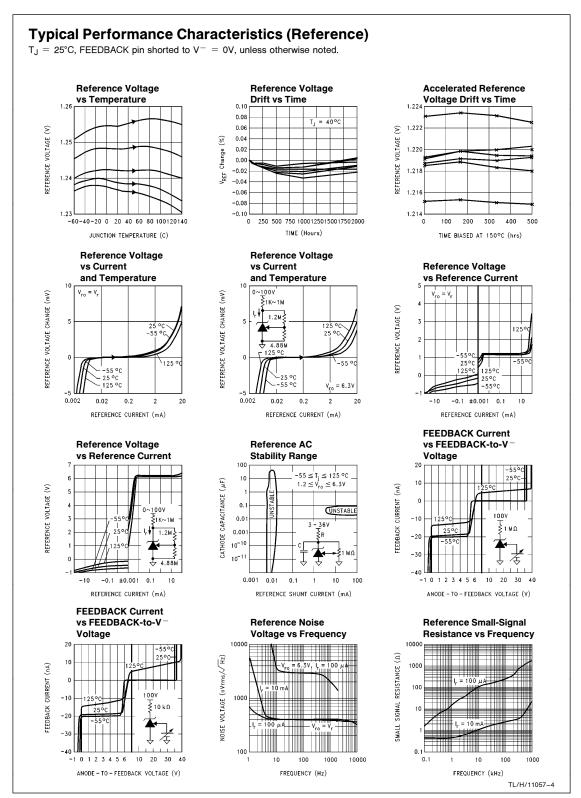
Note 9: V<sub>RO</sub> is the reference output voltage, which may be set for 1.2V to 6.3V (see Application Information). V<sub>R</sub> is the V<sub>RO</sub>-to-FEEDBACK voltage (nominally 1.244V).

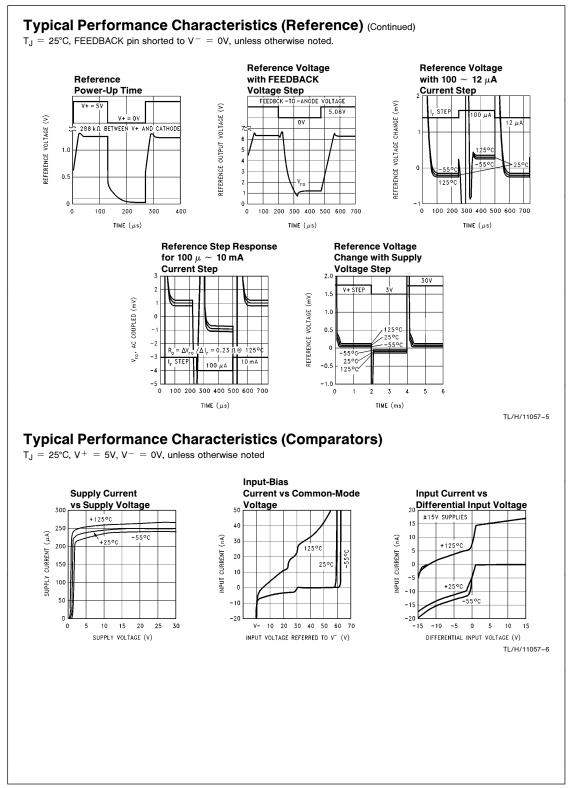
Note 10: Average reference drift is calculated from the measurement of the reference voltage at 25°C and at the temperature extremes. The drift, in ppm/°C, is  $10^6 \bullet \Delta V_R/V_{R[25^\circ C]} \bullet \Delta T_J$ , where  $\Delta V_R$  is the lowest value subtracted from the highest,  $V_{R[25^\circ C]}$  is the value at 25°C, and  $\Delta T_J$  is the temperature range. This parameter is guaranteed by design and sample testing.

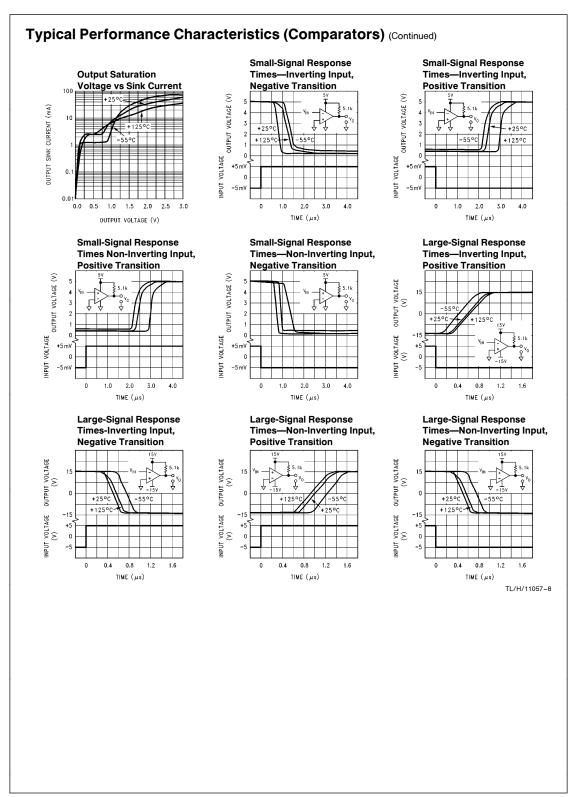
Note 11: Hysteresis is the change in V<sub>RO</sub> caused by a change in T<sub>J</sub>, after the reference has been "dehysterized." To dehysterize the reference; that is minimize the hysteresis to the typical value, its junction temperature should be cycled in the following pattern, spiraling in toward 25°C: 25°C, 85°C, -40°C, 70°C, 0°C, 25°C. Note 12: Low contact resistance is required for accurate measurement.

Note 13: A military RETS electrical test specification is available on request. The LM615AMJ/883 may also be procured as a Standard Military Drawing.





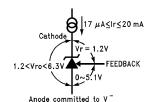




#### **Application Information** VOLTAGE REFERENCE

#### **Reference Biasing**

The voltage reference is of a shunt regulator topology that models as a simple zener diode. With current Ir flowing in the "forward" direction there is the familiar diode transfer function.  $I_r$  flowing in the reverse direction forces the reference voltage to be developed from cathode to anode. The cathode may swing from a diode drop below  $\mathsf{V}^-$  to the reference voltage or to the avalanche voltage of the parallel protection diode, nominally 7V. A 6.3V reference with  $V^+$  = 3V is allowed.



#### FIGURE 1. Voltage Associated with Reference (Current Source Ir is External)

TI /H/11057-9

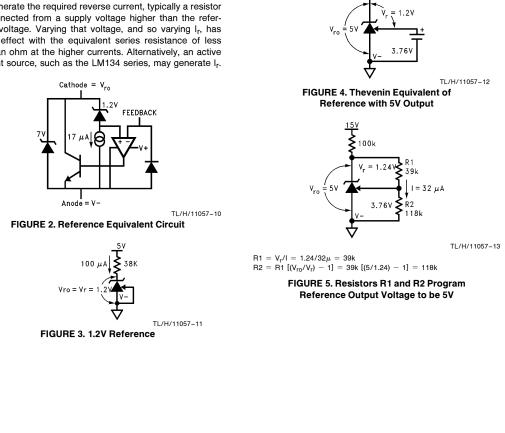
The reference equivalent circuit reveals how Vr is held at the constant 1.2V by feedback, and how the FEEDBACK pin passes little current.

To generate the required reverse current, typically a resistor is connected from a supply voltage higher than the reference voltage. Varying that voltage, and so varying  ${\sf I}_r$ , has small effect with the equivalent series resistance of less than an ohm at the higher currents. Alternatively, an active current source, such as the LM134 series, may generate Ir.

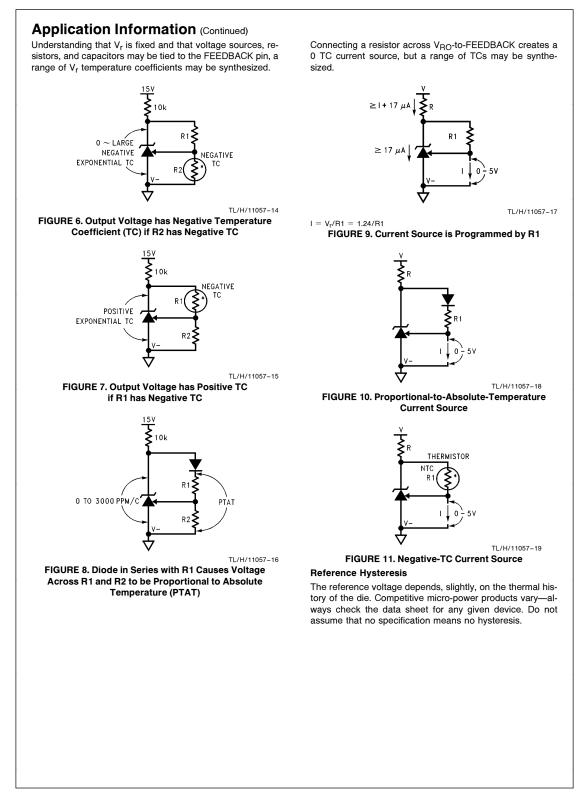
Capacitors in parallel with the reference are allowed. See the Reference AC Stability Range typical curve for capacitance values-from 20 µA to 3 mA any capacitor value is stable. With the reference's wide stability range with resistive and capacitive loads, a wide range of RC filter values will perform noise filtering.

#### **Adjustable Reference**

The FEEDBACK pin allows the reference output voltage, Vro, to vary from 1.24V to 6.3V. The reference attempts to hold  $V_r$  at 1.24V. If  $V_r$  is above 1.24V, the reference will conduct current from Cathode to Anode; FEEDBACK current always remains low. If FEEDBACK is connected to Anode, then  $V_{ro} = V_r = 1.24V$ . For higher voltages FEED-BACK is held at a constant voltage above Anode-say 3.76V for  $V_{ro} = 5V$ . Connecting a resistor across the constant V<sub>r</sub> generates a current I =  $R1/V_r$  flowing from Cathode into FEEDBACK node. A Thevenin equivalent 3.76V is generated from FEEDBACK to Anode with R2 = 3.76/I. Keep I greater than one thousand times larger than FEED-BACK bias current for <0.1% error—I  $\geq$  32  $\mu$ A for the military grade over the military temperature range (I  $\geq$  5.5  $\mu A$ for a 1% untrimmed error for an industrial temperature range part).



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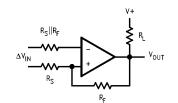
# Application Information (Continued)

#### COMPARATORS

Any of the comparators or the reference may be biased in any way with no effect on the other sections of the LM615, except when a substrate diode conducts (see Electrical Characteristics Note 3). For example, one or both inputs of one comparator may be outside the input voltage range limits, the reference may be unpowered, and the other comparators will still operate correctly. Unused comparators should have inverting input and output tied to V<sup>-</sup>, and non-inverting input tied to V<sup>+</sup>.

#### Hysteresis

Any comparator may oscillate or produce a noisy output if the applied differential input voltage is near the comparator's offset voltage. This usually happens when the input signal is moving very slowly across the comparator's switching threshold. This problem can be prevented by the addition of hysteresis, or positive feedback, as shown in *Figure 12*.



TL/H/11057-20 FIGURE 12. R<sub>S</sub> and R<sub>F</sub> Add Hysteresis to Comparator The amount of hysteresis added in *Figure 12* is

$$V_{H} = V^{+} x \frac{R_{S}}{(R_{F} + R_{S})}$$
  
 $\approx V^{+} x \frac{R_{S}}{R_{F}} \text{ for } R_{F} \gg$ 

A good rule of thumb is to add hysteresis of at least the maximum specified offset voltage. More than about 50 mV of hysteresis can substantially reduce the accuracy of the comparator, since the offset voltage is effectively being increased by the hysteresis when the comparator output is high.

Rs

It is often a good idea to decrease the amount of hysteresis until oscillations are observed, then use three times that minimum hysteresis in the final circuit. Note that the amount of hysteresis needed is greatly affected by layout. The amount of hysteresis should be rechecked each time the layout is changed, such as changing from a breadboard to a P.C. board.

#### Input Stage

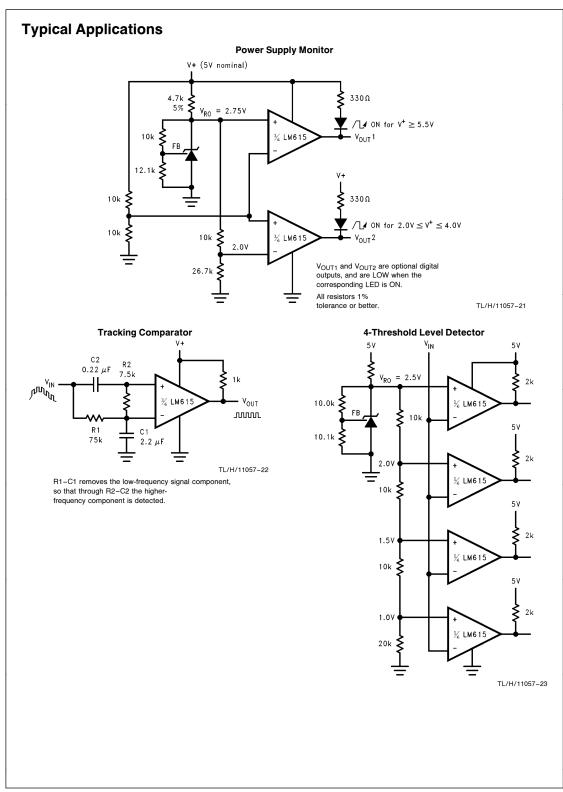
The input stage uses lateral PNP input transistors which, unlike those of many op amps, have breakdown voltage  $BV_{EBO}$  equal to the absolute maximum supply voltage. Also, they have no diode clamps to the positive supply nor across the inputs. These features make the inputs look like high impedances to input sources producing large differential and common-mode voltages.

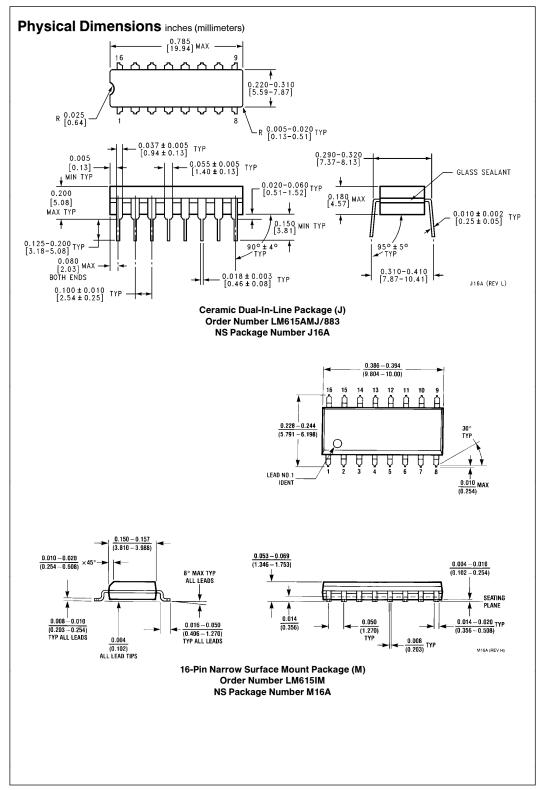
The guaranteed common-mode input voltage range for an LM615 is V<sup>-</sup>  $\leq$  V<sub>CM</sub>  $\leq$  (V<sup>+</sup> - 1.8V), over temperature. This is the voltage range in which the comparisons must be made. If both inputs are within this range, the output will be at the correct state. If one input is within this range, and the other input is less than (V<sup>-</sup> + 32V), even if this is greater than V<sup>+</sup>, the output will be at the correct state. If, however, either or both inputs are driven below V<sup>-</sup>, and either input current exceeds 10  $\mu$ A, the output state is not guaranteed to be correct.

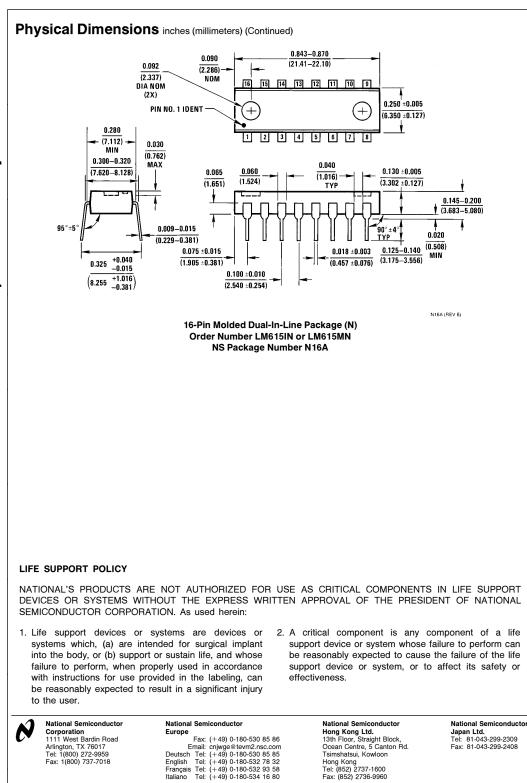
#### **Output Stage**

The comparators have open-collector output stages which require a pull-up resistor from each output pin to a positive supply voltage of the output to switch properly. When the internal output transistor is off, the output (HIGH) voltage will be pulled up to this external positive voltage.

To ensure that the LOW output voltage is under the TTL-low threshold, the output transistor's load current must be less than 0.8 mA (over temperature) when it turns on. This impacts the minimum value of the pull-up resistor.







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